Supporting Information

Inorganic molecule-induced electron transfer complex for highly efficient organic solar cells

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S1. Materials

The polymer donor PBDB-T-2F and the non-fullerene acceptor Y6 and PFN-Br were purchased from Solarmer Materials (Beijing) Inc. The processing solvents used in the device fabrication processes were purchased from Alfa Aesar and were all commercially available anhydrous solvents. Poly(3,4- ethylenedioxythiophene): poly (styrenesulfonate) (PEDOT:PSS) (AI 4083) and electrode materials were commercially available products without further purification.

S2. Device Fabrication

The spin-coated and blade-coated OSC devices were fabricated and characterized by using a conventional structure of ITO/PEDOT:PSS or PMCs/active layer/PFN-Br/Al, where the PEDOT:PSS and PMCs were all served as the anode interlayers. The ITO substrates were cleaned with detergent water, deionized water, acetone and isopropyl alcohol in an ultrasonic bath sequentially for 20 minutes, and then dried in an oven at 150 °C for 30 minutes.

Anode interlayers fabrication. After substrates were treated by UV-ozone for 20 min, PEDOT:PSS was coated at 4,000 rpm for 60 s and then annealed for 15 min at 150 °C in the air. For PMCs as the interlayers, PMCs were dissolved in methanol and then coated on ITO substrates without annealing.

Active layer fabrication. PBDB-T-2F:Y6 (1:1.2, w/w) blend was dissolved in chloroform (CF) solvent at a polymer weight concentration of 7 mg/mL and 0.5% volume 1-chloronaphthalene (CN) was used as the solvent additive. Then 0.5 mg/mL PFN-Br in methanol was spin-coated on the top of active layer at 3,000 rpm for 30 s. Finally, about 100 nm Al were thermally evaporated under a vacuum at a pressure of 3×10^{-4} Pa, giving an area of 0.04 cm² and 1.0 cm². Except for the spin-coating of PEDOT:PSS, the other the processes were all carried out in an nitrogen-filled glovebox.

S3. Device Characterization

The *J*–*V* measurement was performed via the solar simulator (SS-F5-3A, Enlitech) along with AM 1.5 G spectra whose intensity was calibrated by the certified standard silicon solar cell (SRC-2020, Enlitech) at 100 mW/cm². The EQE spectrum was measured using a QE-R3011 Solar Cell Spectral Response Measurement System (Enli Technology Co., Ltd., Taiwan). The film thickness data was obtained via a surface profilometer (Dektak XT, Bruker). UV-vis absorption spectra were measured by Hitachi UH4150 spectrophotometer. XPS was performed on the Thermo Scientific ESCALab 250Xi using 200 W monochromated Al K_α radiation. UPS was carried out on Thermo Scientific ESCALab 250Xi using a He discharged lamp. AFM height and phase images were recorded on a Nanoscope V AFM microscope (Bruker), where the tapping mode was used. X-ray diffraction (XRD) patterns were collected using a Rigaku D/max 2500 X-ray diffractometer.

S4. Additional Fig.s and Tables

The structural characteristics of these five PMCs are identified using measurements of powder X-ray diffraction (XRD) patterns, as shown in Fig. S1. The Bragg reflection peaks in four ranges of 2θ at 7–10°, 14–22°, 25–30° and 31–35° are the typical characteristic peaks of the Keggin-type structure.¹ The IR spectra of these five PMCs exhibit similar characteristic vibrational features of a typical Keggin structure (Fig. S2): four strong bands are clearly observed at 1079~1064, 982~967, 899~891, and 810~798 cm⁻¹, which are assigned to the symmetric and asymmetric bond stretching modes for P–O, M=O_t, M–O_b–M, and M–O_c–M, respectively, where M denotes the W or Mo atom; O_t denotes the terminal oxygen atom; O_b and O_c denote different bridge oxygen atoms.²



Fig. S1 XRD patterns of (a) PMC-1, (b) PMC-2, (c) PMC-3, (d) PMC-4 and (e) PMC-5.



Fig. S2 Infrared (IR) spectra of the PMCs. The IR peaks at 1079~1064, 982~967, 899~891, and 810~798 cm⁻¹ indicate the symmetric and asymmetric bond stretching modes for P–O, $M=O_t$, $M=O_b-M$, and $M=O_c-M$.



Fig. S3 UPS spectra of (a) bare ITO substrate, ITO covered with (b) PEDOT:PSS, (c) PMC-1, (d) PMC-2, (e) PMC-3, (f) PMC-4 and (g) PMC-5, and (h) the pure PBDB-T-2F film.



Fig. S4 *I-V* characteristics of longitudinal conductivity measurements for (a) the PMCs and (b) PEDOT:PSS.



Fig. S5 AFM images of (a) bare ITO substrate and ITO covered with (b) PMC-1, (c) PMC-2, (d) PMC-3, (e) PMC-4 and (f) PMC-5.



Fig. S6 Contact angle measurements of (a) bare ITO substrate and ITO covered with (b) PMC-1, (c) PMC-2, (d) PMC-3, (e) PMC-4, and (f) PMC-5 using chloroform.



Fig. S7 (a) Chemical structures of PBDB-T, PBDB-T-2F, J52-2F, PTB7-Th, ITIC, IT-4F, IT-M, PC₇₁BM. (b)-(e) *J-V* curves of different active layers use PMC-4 as AIL.



Fig. S8 ESR spectra of pure PBDB-T-2F and solid mixtures of PBDB-T-2F with (a) PMC-1, (b) PMC-2, (c) PMC-3, (d) PMC-4 and (e) PMC-5.



Fig. S9 The chemical structure of P3HT, PBDB-T, PBDB-T-2F and PBDB-T-4F.



Fig. S10 Photo-CELIV measurement of PMC-4 and PEDOT:PSS devices.

Furthermore, to illustrate the capacity of the PMCs in modifying the efficient active layer, we evaluated the built-in voltage (V_{bi}) of PMC-modified devices by employing Mott-Schottky analysis.³ Fig. S11 shows the *C-V* characteristics obtained by applying a low AC perturbation signal with fixed frequency and sweeping the DC bias. The V_{bi} values are determined to be 0.59, 0.60, 0.60, 0.59, 0.59, and 0.57 V for the devices with PMC-1, PMC-2, PMC-3, PMC-4, PMC-5 and PEDOT:PSS, respectively. The V_{bi} values of the PMC-based devices are higher than that of the PEDOT:PSS device, meaning that the ideal internal electric fields can be achieved in the PMC-modified OSCs. Since the V_{bi} is an important parameter to evaluate the upper limit for the V_{oc} , the high V_{bi} may be responsible for the high V_{oc} in the PMC-modified OSCs.



Fig. S11 Mott-Schottky analysis of devices with PEDOT:PSS and the PMCs.



Fig. S12 2 $\mu m \times$ 2 μm AFM images of five different spots collected along the diagonal line of a 1cm² PMC-4 film.



Fig. S13 J-V and EQE curves of devices with PMCs thicknesses at 20 and 40 nm.

中国计量科学研究院

测 试 报 Test Report 告

报告编号 GXtc2019-1446 Report No.

| 客户名称 Client | 中国科学院化学研究所 |
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| Client | Institute of Chambridge Chinese And and the Const |
| | Institute of Chemistry Chinese Academy of Science |
| 样品复数 | 有机太阳能电池 |
| Sample | Organic Solar Cell |
| III - (+ta +tr | 非富勒烯聚合物太阳能电池 |
| Type/Model | Non-fullerene polymer solar cell |
| 出厂编号 | 2// NIX / X //2/ 12 /2 |
| Serial No. | 2#-NIM MS06-F-02 |
| 生产厂商 | 中国科学院化学研究所 |
| Manufacturer | Institute of Chemistry Chinese Academy of Science |
| 家白粉朴 | 北京市海淀区中关村北一街2号 |
| Client Address | No.2 1st North Street Zhongguancun Beijing P.R.China |
| 测试日期 | 2019-06-06 |
| Manufacturer 客户地址 Client Address 测试日期 Date of Test | Institute of Chemistry Chinese Academy of Science 北京市海谈区中关村北一街 2 号 No.2 1st North Street Zhongguancun Beijing P.R.Ch 2019-06-06 |

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中国计量科学研究院 报告编号 GXtc2019-1446 Transensus rippents) 環境不発意体入設点Testing place and environment: 器 度 (24.5 ±) ℃ 推 点Location:中国計量院光学楼 110 室 譜 度 Humidity: (57.8 ± 2) % NHT 其 它 Others: / 器 成使用的计量基 (标) 准範型 (含标准物語)±要仪器 Reference Standards (Including Reference Material) / Inst 名 称 Name 潮量范围 Reasurement Range Uncertainty/Accuracy 证书有效期至 证书编号 Certificate No. Due Date (YYYY-MM-DD) 标准太阳电池 L: (0-200) m/ 0.9% (k=2) GXtc2019-0411 2020-03-06 oell 小面积稳态太阳 模拟器 Steady solar simulator (300-1100) nm AAA 22 GXtc2019-022 2020-02-13 DC-V 演奏 0mV-10V (5×10*4-10×10*5) (k=2) 2020-01-03 DC-I:100µA-1A (10×10⁻⁶-40> 2019-c 第2页 共4页 中国计量科学研究院 报告编号 GXtc2019-1446 测试结果 Test Results 有效面积 領路由流 开路由压 最大功率 (mm²) 64.070 V_{oc}(V) 0.833

中国计量科学研究院 报告编号 GXtc2019-1446 Report No. 测试结果 Test Results
 Test Results

 1. 製试条件 Test Conditions:

 第港太阳地先, 角晶位 (819);

 Reference Solar Cell: mono-Si (819);

 太阳梯松器, 死洗環太阳環辺路, AAA 度;

 Solar Simulator Classification;

 高度(体器和包括系统, 近, 行行時間);

 Teperature Senser/Control System: None;

 目前力前, 正扫

 Scan Direction:Forward

 也比亞, Color Joint Ove-0.90V; 间隙, 0.01V

 Scan Parameter: From -0.10V to 0.90V with 0.01V interval

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 当師封前; 31 使 扫描点版, 101

 Scan Time: 31 s
 Scan Point: 101
 I-V 特性參数 I-V Characteristic parameters: 以上述标准太阳电池标定太阳模拟器幅照度至 1000 W/m², 校准被调太阳电 池的 I-V 特性曲线和参数如下;
 By using the above reference solar cell to calibrate the solar simulator's irradiance to 1000 W/m², the I-V characteristic curve and parameters as follows: 0.020 I-V 0.01 Power (M) 0.010 0.6 Voltage (V) 2019-cs 第3页 共4页

I6.06 取入功率 Pmax(mW) 9.133 转换效率(PCE) 最大功率电流 Imax(mA) 最大功率电压 Vmax(V) 填充因子

FF (%)

68.3

η(%)

14.3

注 Note Process in Coll Resident an 当时状态有效。
 The data apply only at the time of the test for the sample.
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0.650

14.05

测试员: 孟强励

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> Checked by 第4页 共4页

核验员: 永仪超

2019.05

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Fig. S14 Certification report of large-area device (0.8 cm×0.8 cm mask) from National Institute of Metrology (NIM).



Fig. S15 The PCE for PEDOT:PSS and PMCs-based solar cells as a function of storage time in glove box.



Fig. S16 *J*-*V* curves of 1cm² devices based on PMCs.



Fig. S17 J-V and EQE curves of PEDOT:PSS based devices (0.04cm²).

Table S1. Photovoltaic parameters of devices based on other different anode interlayers with the same active layer (PBDB-T-2F: IT-4F).

| AILs | $V_{ m oc}$ (V) | $J_{\rm sc}~({\rm mA/cm^2})$ | FF | PCE (%) |
|------------------|-----------------|------------------------------|------|-------------------|
| PEDOT:PSS | 0.87 | 20.38 | 0.77 | 13.7 4 |
| MoO ₃ | 0.81 | 17.9 | 0.74 | 10.8 |
| PCP-3B | 0.79 | 19.7 | 0.73 | 11.3 |
| PCP-Na | 0.71 | 20.1 | 0.65 | 9.32 ⁵ |

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|-------|-----------------------------|---------------------|------------------------------|------|---------|
| | Active layer | V _{oc} (V) | $J_{\rm sc}~({\rm mA/cm^2})$ | FF | PCE (%) |
| - | PBDB-T:ITIC | 0.90 | 16.8 | 0.71 | 10.7 |
| | PBDB-T-2F:IT-4F | 0.84 | 21.1 | 0.75 | 13.2 |
| | J52-2F:IT-M | 0.95 | 18.2 | 0.71 | 12.2 |
| | PTB7-Th:PC ₇₁ BM | 0.80 | 16.8 | 0.66 | 8.86 |

Table S2. Photovoltaic parameters of devices based on PMC-4 films with different active layers.

| Table S3. Photovoltaic | parameters | of devices | based on PM | IC films | with | different | thicknesses. |
|------------------------|------------|------------|-------------|----------|------|-----------|--------------|
|------------------------|------------|------------|-------------|----------|------|-----------|--------------|

| AILs | Thickness | V _{oc} (V) | J _{sc} (mA/cm ²) | FF | PCE (%) | $\frac{J_{\rm cal}{}^a}{({\rm mA/cm}^2)}$ |
|-------|-----------|---------------------|--|-------|------------|---|
| DMC 1 | 20 nm | 0.826 | 24.52 | 0.628 | 12.72 | 24.18 |
| PMC-1 | 40 nm | 0.842 | 24.81 | 0.409 | 8.54 | 24.58 |
| DMC 2 | 20 nm | 0.845 | 24.20 | 0.697 | 14.25 | 23.64 |
| PMC-2 | 40 nm | 0.841 | 23.87 | 0.668 | 13.41 | 23.62 |
| DMC 3 | 20 nm | 0.839 | 24.39 | 0.679 | 14.25 | 24.04 |
| PMC-3 | 40 nm | 0.854 | 23.31 | 0.660 | 13.14 | 22.73 |
| | 20 nm | 0.845 | 22.82 | 0.738 | 14.24 | 22.54 |
| PMC-4 | 40 nm | 0.843 | 22.70 | 0.704 | 13.47 | 22.14 |
| DMC 5 | 20 nm | 0.804 | 17.27 | 0.625 | 8.68 | 16.59 |
| PMC-5 | 40 nm | 0.797 | 15.06 | 0.222 | 2.67 | 14.40 |

^{*a*}Integrated J_{cal} from the EQE curves.

 Table S4. The fitting results of the Nyquist plots of PMC AILs devices.

| PMC-1 236 54933 4.30E-9 | 21735 | 3.87E-9 |
|-----------------------------------|-------|---------|
| PMC-2 29.08 111 3.13E-9 | 30.91 | 1.49E-8 |
| PMC-3 79.07 82.664 5.37E-9 | 22.68 | 2.65E-8 |
| PMC-4 47.51 107.7 4.44E-9 | 14.71 | 4.81E-8 |
| PMC-5 320.6 85208 3.34E-9 | 49940 | 2.15E-9 |

| Table S5. | The | PCEs | (%) | of 30 | cells | for | 1.0 cr | n². |
|-----------|-----|------|-----|-------|-------|-----|--------|-----|
|-----------|-----|------|-----|-------|-------|-----|--------|-----|

| No.1 | No.2 | No.3 | No.4 | No.5 | No.6 | No.7 | No.8 | No.9 | No.10 |
|------|------|------|------|------|------|------|------|------|-------|
|------|------|------|------|------|------|------|------|------|-------|

| 15.08 | 15.03 | 14.83 | 14.89 | 14.85 | 14.71 | 14.61 | 14.62 | 14.54 | 14.93 |
|-------|-------|-------|-------|-------|-------|-------|-------|-------|-------|
| No.11 | No.12 | No.13 | No.14 | No.15 | No.16 | No.17 | No.18 | No.19 | No.20 |
| 14.81 | 14.68 | 14.64 | 14.60 | 13.84 | 13.25 | 14.85 | 14.92 | 14.48 | 14.49 |
| No.21 | No.22 | No.23 | No.24 | No.25 | No.26 | No.27 | No.28 | No.29 | No.30 |
| 14.50 | 14.55 | 13.35 | 14.52 | 14.77 | 14.93 | 14.39 | 14.77 | 14.09 | 14.52 |

Table S6. Photovoltaic parameters of 1cm² devices based on PMCs.

| PMCs | V _{oc} (V) | $J_{\rm sc}$ (mA/cm ²) | FF | PCE (%) |
|-------|---------------------|------------------------------------|-------|---------|
| PMC-1 | 0.835 | 24.32 | 0.662 | 13.43 |
| PMC-2 | 0.832 | 25.32 | 0.703 | 14.81 |
| PMC-3 | 0.843 | 25.48 | 0.701 | 15.05 |
| PMC-4 | 0.836 | 25.46 | 0.707 | 15.08 |
| PMC-5 | 0.809 | 22.97 | 0.488 | 9.08 |

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